

北京大学量子材料科学中心

International Center for Quantum Materials, PKU

Seminar

Low dimensional hybrids and their novel gate-tunable quantum properties

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Time: 4:00Pm, Sep. 12, 2018 (Wednesday) 时间: 2018年09月12日 (周三)下午4:00 Venue: Room W563, Physics building, Peking University 地点: 北京大学物理楼,西563会议室

Abstract

Electrostatic gate tuning of quantum properties has been the key of mesoscopic physics. Especially, when the thickness of a system become negligible (i.e., the 2D limit), Coulomb screening is strongly suppressed and thus gate tuning can directly affect/shift its Fermi level, leading to a tremendous variety of emerging phenomena.

In this talk, we will first go through our previous works on quantum properties of the 2D materials/h-Boron-Nitride nano-hybrid systems.[1-2] Our recent studies on the electro-static gate tuning of an intrinsic ferromagnetic semiconductor in the 2D limit will also be discussed.[3] We expect that artificial nano-hybrids and their quantum properties can be expanded into many research areas that are important for both fundamental studies and future applications.

[1] S. Chen, Z. Han (equal contributor), et al., Science, 353, 1522 (2016).

- [2] X. X. Li, ..., Z. Han*, et al., Nature Communications, 8, 970 (2017).
- [3] Z. Wang, ..., Z. Han^{*}, et al., Nature Nanotechnology, 13, 554 (2018).

About the speaker

Zheng Vitto Han got his PhD in nanoelectronics at N éel Institute, and is now a research professor at the Institute of Metal Research, CAS in Shenyang, China. Dr. Han has been utilizing nanoFab together with artificial staking methods to study the interfacial coupling of low-dimensional materials such as graphene and superconducting nano-dot arrays, MoS₂, and two-dimensional magnetic semiconductors, etc. He has revealed a series of exotic physical properties of such systems, with the related works published in Science, Nature Physics, Nature Nanotechnology and other journals.

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